

	Type	Hits	Search Text	DBs	Time Stamp
1	IS&R	9	("5736767") or ("5314834") or ("5840604") or ("5918114") or ("6040212") or ("6051509") or ("6222232") or ("6222232") or ("5221850") or ("5241194").PN.	USPAT; US-PGPUB	2003/01/22 09:19
2	IS&R	40	("5324966") or ("5654215") or ("5804476") or ("5834352") or ("5885859") or ("5894150") or ("6002154") or ("6001695") or ("6037631") or ("6080630") or ("6087237") or ("6087224") or ("6096586") or ("6110788") or ("6140688") or ("6228698") or ("4358890") or ("4417385") or ("4760431") or ("4908682") or ("4914496") or ("4983538") or ("5200354") or ("5208477") or ("5250447") or ("5279979") or ("5296726") or ("5336943") or ("5414287") or ("5444272") or ("5457061") or ("5460988") or ("5463237") or ("5471075") or ("5488236") or ("5554862") or ("5580799") or ("5604368") or ("5610430") or ("5625213").PN.	USPAT; US-PGPUB	2003/01/22 09:19
3	IS&R	2	("4823173") or ("5264719").PN.	USPAT; US-PGPUB	2003/01/22 09:24
4	BRS	12	5264719.URPN.	USPAT	2003/01/22 09:27
5	BRS	5	("4626879"   "4628341"   "4811075"   "4994889"   "4994904").PN.	USPAT	2003/01/22 09:29
6	BRS	7	("4270137"   "4300150"   "4344080"   "4394674"   "4409606"   "4422089"   "4485392").PN.	USPAT	2003/01/22 09:30
7	BRS	13	4823173.URPN.	USPAT	2003/01/22 09:30
8	BRS	246	lateral adj mosfet	USPAT; US-PGPUB	2003/01/22 11:08
9	BRS	1	(lateral adj mosfet) same (top adj gate)	USPAT; US-PGPUB	2003/01/22 11:06
10	BRS	88	lateral adj mosfet	EPO; JPO; DERWENT; IBM_TDB	2003/01/22 11:08

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 20030006482 A1	17	MOS integrated circuit with reduced on resistance	257/547	257/213; 257/297; 257/356; 257/499	Beasom, James D.
2	US 20020185696 A1	15	Lateral DMOS structure with lateral extension structure for reduced charge trapping in gate oxide	257/409		Beasom, James D.

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L20	44	Idmosfet	USPAT; US-PGPUB	2003/01/22 15:16
2	BRS	L21	52	Idmosfet	EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:16

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 5264719 A	16	High voltage lateral semiconductor device	257/335	257/336; 257/339; 257/E29 04; 257/E29 265; 257/E29 312	Beasom, James D.
2	US 6469346 B1	10	High-breakdown-voltage semiconductor device	257/336	257/195; 257/343; 257/344	Kawaguchi, Yusuke et al.
3	US 5763927 A	12	High-voltage lateral field effect transistor having auxiliary drain electrode for a step-down drain voltage	257/408	257/343; 257/344; 257/491; 257/E29 013; 257/E29 268	Koishikawa, Yukimasa
4	US 5512495 A	11	Method of manufacturing extended drain resurf lateral DMOS devices	438/286	148/DIG. 126; 257/E29 268; 438/298	Mei, Chia-Cu P. et al.
5	US 4823173 A	8	High voltage lateral MOS structure with depleted top gate region	257/262	257/279; 257/409; 257/E29 04; 257/E29 265; 257/E29 312	Beasom, James D.
6	US 4994904 A	27	MOSFET having drain voltage detection function	257/212	257/336; 257/339; 257/E29 054; 257/E29 197; 257/E29 198	Nakagawa, Akio et al.
7	US 4811075 A	6	High voltage MOS transistors	257/369	257/408; 257/409; 257/492; 257/E27 059; 257/E27 065; 257/E29 04; 257/E29 064; 257/E29 268	Eklund, Klas H.
8	US 4300150 A	5	Lateral double-diffused MOS transistor device	257/336	257/339; 257/901; 257/E29 013; 257/E29 062; 257/E29 063; 257/E29 256	Colak, Sel
9	US 5322804 A	17	Integration of high voltage lateral MOS devices in low voltage CMOS architecture using CMOS-compatible process steps	438/227	257/E29 268; 438/286; 438/298	Beasom, James D.

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
10	US 5311051 A	12	Field effect transistor with offset region	257/409	257/339; 257/E29.04; 257/E29.268	Tukizi Masaru

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 5221850 A	9	Conductivity-modulating MOSFET	257/173	257/139; 257/147; 257/168	Sakurai Kenya
2	US 5894150 A	18	Cell density improvement in planar DMOS with farther-spaced body regions and novel gates	257/335	257/329; 257/339; 257/E27 06; 257/E29 01; 257/E29 066; 257/E29 257	Hsieh, Fwu-luan
3	US 5444272 A	12	Three-terminal thyristor with single MOS-gate controlled characteristics	257/137	257/132; 257/133; 257/138; 257/146; 257/154; 257/163; 257/E29 214; 257/E29 216; 257/E29 219	Ajit, Janardhanan S.
4	US 4914496 A	17	Gate turn-off thyristor with independent turn-on/off controlling transistors	257/138	257/142; 257/144; 257/157	Nakagawa, Akio et al.
5	US 4908682 A	8	Power MOSFET having a current sensing element of high accuracy	257/336	257/E29 027; 257/E29 257	Takahashi, Mitsuasa
6	US 4760431 A	16	Gate turn-off thyristor with independent turn-on/off controlling transistors	257/138	257/142; 257/144; 257/157; 257/E29 214; 257/E29 216; 257/E29 223	Nakagawa, Akio et al.

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